

Sample Final (Spring 2000 Final) (Solutions)

a) $I_{D3} = 50 \mu A = \frac{\mu_n C_{ox} (\frac{W}{L})_3 (V_{GS3} + V_{TP})^2}{2 \mu_n \mu_0^2}$

Solving for V_{GS3} , $V_{GS3} = 1.5V \Rightarrow \overline{V_{GNTT3}} = 2.5 - 1.5 = 1V$

$I_{D4} = 100 \mu A = \mu_n C_{ox} (\frac{W}{L})_4 (V_{GS4} - V_{TN})^2$

Solving for V_{GS4} , $V_{GS4} = 1.5V \Rightarrow \overline{V_{GNTT4}} = -2.5V + 1.5V = -1V$

b) $V_{OUT} = \sqrt{\frac{2 I_{D1}}{\mu_n C_{ox} (W/L)_1}} + V_{TN}$

$V_{GS1} = -V_{TP} + \sqrt{\frac{2 I_{D1}}{\mu_n C_{ox} (W/L)_1}} + V_{TN}$

$V_{GS2} = \sqrt{\frac{2 I_{D2}}{\mu_n C_{ox} (W/L)_2}} + V_{TN}$

$(W/L)_2 = \frac{2 I_{D2}}{\mu_n C_{ox} (V_{GS2} - V_{TN})^2} = \frac{2 (100 \mu A)}{(50 \mu A / \mu^2) (1.5 - 1.261)^2} = 70.2 \Rightarrow \overline{W}_2 = 140.3 \mu m$

Use worst $\overline{V_{GNTT3}} = 1V$ and $\overline{V_{GNTT4}} = -1V$ as found in part a. One way to solve for the size of m_5 is to use what we know in part a.

In part a, $I_{REF} = 50 \mu A$ and in order to have the same $\overline{V_{GNTT3}}$, $(W/L)_5 = \frac{1}{2} (W/L)_3 = 16/2$.

\rightarrow which leads to the same V_{GS6}

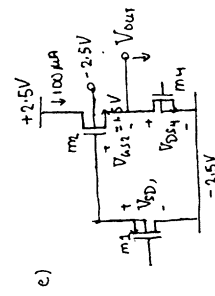
make m_6 the same size as m_5 for convenience. We then know $|I_{D6}| = 25 \mu A = I_{D7}$ as in part a but I_{D6} is now scaled by $\frac{1}{4}$.

$\therefore (W/L)_7 = \frac{1}{4} (W/L)_4 = 8/2$

Combinations of the following will work too.

$(W/L)_5 = (16/2)$, $(W/L)_6 = (4/2)$, $(W/L)_7 = (32/2)$

$(W/L)_5 = (16/2)$, $(W/L)_6 = (8/2)$, $(W/L)_7 = (4/2)$



The 1st thing we need to check for $V_{out, min}$ is whether we keep m_4 in saturation.

$V_{GS4 (sat)} = V_{GS4} - V_{TN} = 1.5 - 1 = 0.5V$

$\therefore V_{out, min} = V_{GS4 (sat)} = -2.5V = -2V$

But this may be too low for the left side to be in saturation. Let's check m_1 .

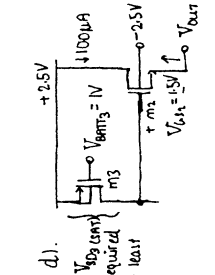
$V_{GS1, min} = V_{GS1} = -2.5V + V_{GS0 (sat)}$

$= -2.5 + 1.5 - 1 = -2V$

Again we need $V_{GS2} = 1.5V$ to keep $I_{D2} @ 100 \mu A$.

$\therefore V_{out, min}$ in this case is $V_{GS1, min} = -1.5V = -3.5V$

$\therefore V_{out, min} = -2V$



$V_{GS3 (sat)} = 1.5V - 1V = 0.5V$

$V_{out, max} = (2.5V - 0.5V) - 1.5V$

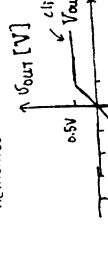
V_{GS2} required to keep I_{D2} at $100 \mu A$

$\therefore V_{out, max} = 0.5V$

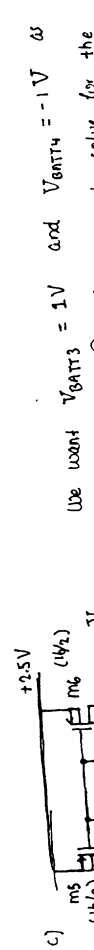
f) $V_{out} = V_{IN} + V_{GS1} - V_{GS2} \approx V_{IN}$

Looks like $CD \approx CD$ amp. V Buffer.

Remember the max & min output voltage.



$\therefore V_{out, min} = -2V$



Using Thevenin technique, $V_{th} = V_s \frac{R_2}{R_1 + R_2}$

$V_{GS} = \frac{R_1 R_2}{R_1 + R_2} \Rightarrow V_{GS} = V_s \frac{R_2}{R_1 + R_2} + V_{out}$

Standard one-pole eq: $\frac{V_{out}}{V_s} \approx \left(\frac{R_1}{R_1 + R_2} \right) \left(\frac{1}{1 + j\omega/\omega_{3dB}} \right)$

$\omega_{3dB} = (R_1 || R_2) (C_w + C_L)$

b) $|V_{out}|_{\omega \rightarrow 0} = R_{vOC} = \frac{R_2}{R_1 + R_2} = \frac{10}{10 + 50} = \frac{1}{6}$

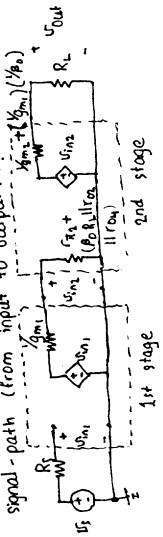
$\omega_{3dB} = \frac{1}{(10k\Omega || 50k\Omega)(100 + 500) pF} = 200 \text{ M rad/sec} = 2\pi (31.8 \text{ MHz})$

$\angle V_{out}/V_s = -\tan^{-1} \left(\frac{\omega}{\omega_{3dB}} \right) = -\tan^{-1} \left(\frac{2\pi (25 \text{ MHz})}{2\pi (31.8 \text{ MHz})} \right) = -38^\circ$

$\therefore V_{out}(t) = \frac{25 \text{ mV}}{6} \cos [2\pi (25 \text{ MHz}) t - 38^\circ]$

4.2 mV

2c) Both stages look CD-ish and CC-ish respectively. Trace the transistor in the signal-path (from input to output)!! In this problem, they are m1 and m2.

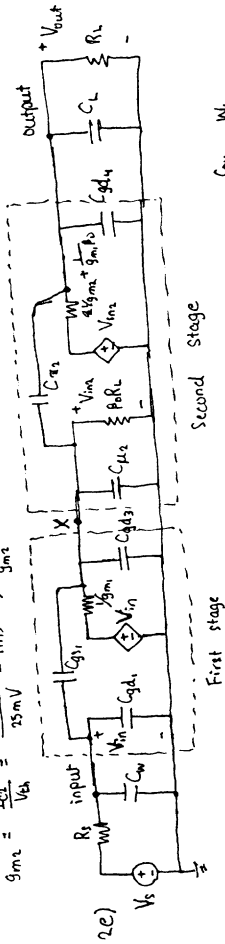


$$2d) \frac{V_{out}}{V_s} = \left[\frac{R_L}{r_{e2} + \beta_0 R_L} \right] \left[\frac{R_L}{\left(\frac{R_L}{\beta_0 g_{m1}} + \beta_0 R_L \right) + R_L} \right] \approx 1 \approx 0.966$$

$$g_{m1} = \sqrt{2 \mu_n C_{ox} (W/L)_1 I_{D1}} = \sqrt{2 (0.5) (16) (50)} = 200 \mu S$$

$$\beta_0 R_L = 5000 \Omega \ll \beta_0 R_L = (100)(10k\Omega) = 1M\Omega$$

$$g_{m2} = \frac{I_{C2}}{V_{BE}} = \frac{100 \mu A}{75 mV} \Rightarrow \frac{1}{g_{m2}} = 750 \Omega$$



$$2f) \tau_{in} = R_s \left\{ C_{w1} + C_{gd1} + (1 - A_{V1}) C_{gs1} \right\} \left\{ C_{w2} + C_{gd2} + (1 - A_{V2}) C_{gs2} \right\}$$

$$A_{V1} C_{gs1} = A_{V1} = \frac{R_{inCC}}{R_{inCC} + \frac{1}{g_{m1}}} \approx 0.994$$

$$= \frac{960k\Omega}{965k\Omega} \approx 0.994$$

$$\therefore \tau_{in} = (50nS) \{ 100fF + 12.8fF + (1 - 0.994)(98.1fF) \} = (50nS)(113.4fF)$$

$$\therefore \tau_{in} \approx 5.67nS$$

$$2g) \tau_x = \left(\frac{1}{g_{m1}} \right) \left\{ C_{gd3} + C_{K2} + (1 - A_{V2}) C_{m2} \right\} = (50nS)(12.8fF + 25fF + 5.95fF) \Rightarrow \tau_x = 0.219nS$$

$$A_{V2} = \frac{R_L}{\left(\frac{R_L}{\beta_0 g_{m2}} + \beta_0 R_L \right) + R_L} = \frac{10k\Omega}{300\Omega + 10k\Omega} = 0.971$$

$$C_{m2} = C_{JE} + g_{m2} \tau_c = 25fF + (4 \times 10^3 S)(45 \times 10^{-12} s) = 205fF$$

$$C_{K2} = 25fF$$

$$C_{gd3} = C_{gd1} = 12.8fF$$

h) We still need to solve time-constant at output node.

$$\tau_{out} = \left[R_{out} \left(\frac{1}{g_{m2}} + \frac{1}{\beta_0 g_{m1}} \right) \right] (C_{L1} + C_{gd4}) \approx 0.149nS$$

$$\omega_{-3dB} = \frac{1}{\tau_{in} + \tau_x + \tau_{out}} = \frac{1}{5.67 + 0.219 + 0.149} \times 10^9 \text{ rad/sec} \approx 1.66 \times 10^8 \text{ rad/sec}$$

$$\therefore f_{-3dB} = 26.4 \text{ MHz}$$

$$3a) I_A = 40 \mu A \quad \frac{W}{L}_2 = 40 \mu A \left(\frac{8}{4} \right) = 80 \mu A$$

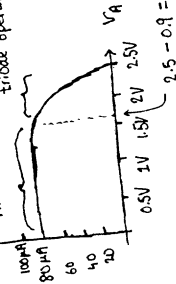
$$b) r_{o2} = r_{o1} = \frac{1}{\lambda \mu_n I_{D2}} \quad \text{where } \lambda \mu_n = \frac{0.1}{L_2} [\mu m] \Rightarrow L_2 = 4 \mu m$$

c) $I_A \approx 80 \mu A$ when m2 is saturated. I_A drops dramatically.

$$\Rightarrow V_{D1SAT} = 0.9V$$

$$V_{SD2SAT} = V_{GS2} + V_{TP} = \sqrt{\frac{2 I_{D2}}{\mu_n C_{ox} (W/L)_2}} = \sqrt{\frac{2 (80)}{2.5(8)}}$$

m2 in sat triode operation of m2



d) $V_A = 1.25V$ ensures that MOSFET is saturated.

$$C_a = C_{db2} + C_{gd2}$$

$$C_{db2} = \frac{C_{j0} W_2 L_{diff}}{\sqrt{1 - (V_{GS2}/\phi_{Si})}} = \frac{(0.2fF/\mu m^2)(32)(6)\mu m^2}{\sqrt{1 - (1.25V/0.9V)}} = 25.6fF$$

$$C_{gd2} = C_{ov} W_2 = (0.4fF/\mu m)(32\mu m) = 12.8fF$$

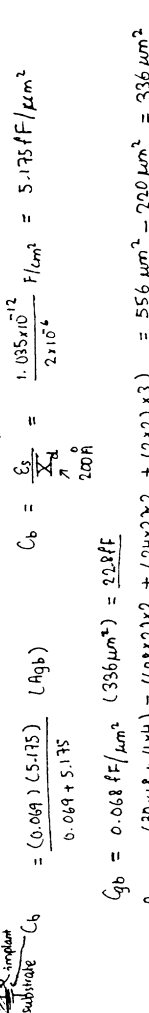
$$C_a = 38.4fF$$

4 d). Triode region with $V_{gs} \ll V_{bc} - V_{Tn}$
 $10mV \ll 250mV$
 $C_{ox} = \frac{\epsilon_{ox}}{t_{ox}} = \frac{3.45 \times 10^{-13}}{1.5 \times 10^{-6}} (F/cm^2) (10^{-8} \frac{cm^2}{\mu m^2})$
 $C_{ox} = 2.3 fF/\mu m^2$

$I_D = \mu_n C_{ox} (W/L) (V_{gs} - V_{Tn})^2 \frac{1}{2}$
 $\approx (375 \frac{cm^2}{Vs}) (2.3 \times 10^{-15} F/\mu m^2) (10^8 \mu m^2/cm^2) (\frac{2}{11.4})^2 (0.25 - 1) (0.01)$
 $I_D \approx 32.8 nA$

e). $C_g = C_{gb} + \frac{1}{2} C_{ox} WL + C_{ov} W$ where $C_{ov} = C_{ox} (L_D)$
 $= (0.069) (5.175) (Agb) + (0.3 fF/\mu m^2) (0.5 \mu m) = 1.15 fF/\mu m$
 $C_{gb} = C_{thox} \frac{C_b}{K}$ in series with C_b
 $= \frac{(0.069) (5.175)}{0.069 + 5.175} (Agb)$ where $C_{thox} = \frac{\epsilon_{ox}}{t_{thox}} = \frac{3.45 \times 10^{-13}}{5 \times 10^{-5}} (F/cm^2) = 69 aF/\mu m^2$
 $C_b = \frac{\epsilon_s}{2 \times 10^{-6}} F/cm^2 = \frac{1.035 \times 10^{-12}}{2 \times 10^{-6}} F/cm^2 = 5.175 fF/\mu m^2$

$C_{gb} = 0.068 fF/\mu m^2 (396 \mu m^2) = 22.8 fF$
 $Agb = (30 \times 18 + 4 \times 4) - ((2.3 \times 2) \times 2 + (2 \times 2) \times 3)$ Channel areas
 $C_g = \frac{1}{2} (2.3) (220) + (1.15 \times 2) = 255.3 fF$
 $\therefore C_g = C_{gb} + C_g = 22.8 fF + 255.3 fF = 278 fF$



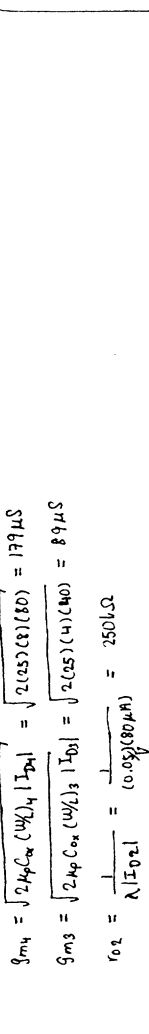
ion-implantation
 junction depth
 0.5 μm in lateral
 direction too

good luck on the final!

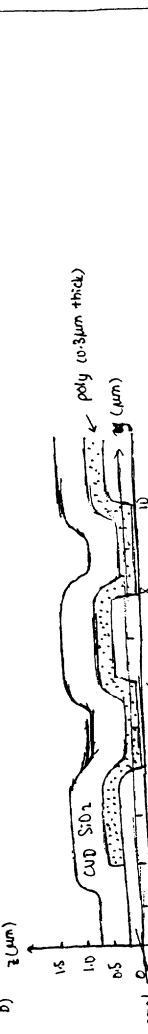
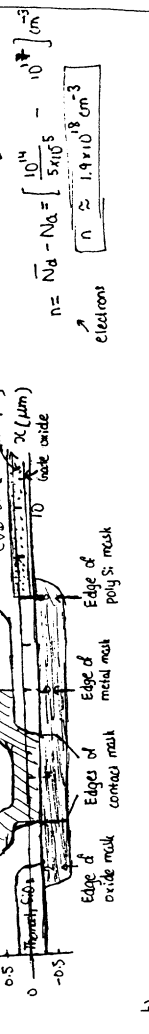
3. c) $Z_{oc} = r_{oc} || j\omega C_a = \frac{r_{oc}}{1 + j\omega C_a r_{oc}}$
 $|Z_{oc}| = \frac{r_{oc}}{\sqrt{1 + (\omega C_a r_{oc})^2}} = \frac{300 k\Omega}{\sqrt{1 + (38.4 k\Omega \cdot 500 rad/s)^2}} \Rightarrow f = 11 MHz$

f) $V_{A,max} = V^+ - V_{S_{04}} - V_{D_{2,STT}}$
 $= 5 - 1.9 - 0.9 = 2.2 V$
 $r_{oc} = r_{o1} (1 + g_{m2} R_{s2}) = 250 k\Omega [1 + (1.9 \times 10^5) (3.74 \times 10^3)] = 417 k\Omega \Rightarrow r_{oc} = 417 k\Omega$

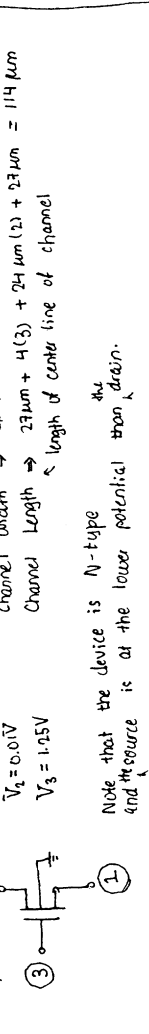
g) $R_{s2} = \frac{1}{g_{m4}} || \frac{1}{g_{m3}} = 5.6 k\Omega || 11.2 k\Omega = 3.74 k\Omega$
 $g_{m4} = \sqrt{2 \mu_n C_{ox} (W/L)_4 I_{D4}} = \sqrt{2 (2.5) (8) (80)} = 179 \mu S$
 $g_{m3} = \sqrt{2 \mu_p C_{ox} (W/L)_3 I_{D3}} = \sqrt{2 (0.5) (4) (40)} = 89 \mu S$
 $r_{o1} = \frac{1}{\lambda |I_{D1}|} = \frac{1}{(0.05) (80 \mu A)} = 250 k\Omega$
 $g_{m2} = g_{m4} = 179 \mu S$



$n = N_d - N_a = \left[\frac{10^{14}}{5 \times 10^{15}} - 10^{17} \right] cm^{-3}$
 $n \approx 1.9 \times 10^{18} cm^{-3}$
 electrons



Operation \Rightarrow Triode
 Channel width $\Rightarrow 2 \mu m$
 Channel length $\Rightarrow 23 \mu m + 4(3) + 24 \mu m (2) + 23 \mu m = 114 \mu m$
 \leftarrow length of center line of channel



Note that the device is N-type and the source is at the lower potential than drain.